

The RF Line NPN Silicon High-Frequency Transistors

... designed for low noise, wide dynamic range front-end amplifiers and low-noise VCO's. Available in a surface-mountable plastic package, as well as the popular TO-226AA (TO-92) package. This Motorola series of small-signal plastic transistors offers superior quality and performance at low cost.

- High Gain-Bandwidth Product
 $f_T = 8.0 \text{ GHz (Typ) @ } 50 \text{ mA}$
- Low Noise Figure
 $NF = 2.0 \text{ dB (Typ) @ } f = 500 \text{ MHz (MMBR571LT1, T3)}$
 $NF(\text{matched}) = 1.6 \text{ dB (Typ) @ } f = 1.0 \text{ GHz (MRF5711LT1, MRF571)}$
- High Gain
 $G_{NF} = 17 \text{ dB (Typ) @ } 30 \text{ mA/500 MHz (MMBR571LT1, T3)}$
- High Power Gain
 $G_{pe}(\text{matched}) = 13.5 \text{ dB (Typ) (MRF5711LT1)}$
- State-of-the-Art Technology
 Fine Line Geometry
 Ion-Implanted Arsenic Emitters
 Gold Top Metallization and Wires
 Silicon Nitride Passivation
- Available in tape and reel packaging options:
 T1 suffix = 3,000 units per reel
 T3 suffix = 10,000 units per reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	10	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage MPS571, MMBR571LT1 MRF5711LT1, MRF571	V_{EBO}	3.0 2.5	Vdc
Collector Current — Continuous MPS571, MMBR571LT1 MRF5711LT1	I_C	80 70	mA
Power Dissipation @ $T_A = 25^\circ\text{C}$ MPS571	P_D	625	mW
Power Dissipation @ $T_{\text{case}} = 75^\circ\text{C}$ MMBR571LT1, MRF5711LT1 Derate linearly above $T_{\text{case}} = 75^\circ\text{C}$ @ MMBR571LT1, MRF5711LT1, T3	$P_{D(\text{max})}$	0.333 4.44	W mW/°C
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C MRF5711LT1	P_D	0.58 4.64	Watts mW/°C
Total Device Dissipation (1) @ $T_C = 75^\circ\text{C}$ Derate above 75°C MRF5711LT1	P_D	0.58 7.73	Watts mW/°C
Total Device Dissipation @ $T_C = 50^\circ\text{C}$ (1) Derate above 50°C MRF571	P_D	1.0 10	Watts mW/°C
Storage Temperature MPS571, MMBR571LT1 MRF5711LT1, MRF571	T_{stg}	-55 to +150 -65 to +150	°C
Maximum Junction Temperature	$T_{J\text{max}}$	150	°C

THERMAL CHARACTERISTICS

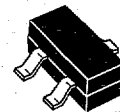
Rating	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient MRF5711LT1	$R_{\theta JA}$	216	°C/W
Thermal Resistance, Junction to Case MRF5711LT1, MMBR571LT1, T3	$R_{\theta JC}$	225	°C/W

DEVICE MARKING

MMBR571LT1, T3 = 7X	MRF5711LT1 = 02
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MMBR571LT1, T3
MPS571 MRF571
MRF5711LT1

$I_C = 80 \text{ mA}$
LOW NOISE
HIGH-FREQUENCY
TRANSISTORS



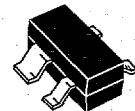
CASE 318-07, STYLE 6
SOT-23
LOW PROFILE
MMBR571LT1



CASE 29-04, STYLE 2
TO-226AA
(TO-92)
MPS571



CASE 317-01, STYLE 2
MACRO-X
MRF571



CASE 318A-05, STYLE 1
SOT-143
LOW PROFILE
MRF5711LT1



ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	10	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 50\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	2.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 8.0\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	10	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 30\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	hFE	50	—	300	—
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DYNAMIC CHARACTERISTICS

Collector-Base Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$) ($V_{CB} = 6.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	MPS571, MMBR571LT1, T3 MRF5711LT1, MRF571	C_{cb}	— —	0.7 0.75	1.0 1.0	pF
Current Gain-Bandwidth Product ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 50\text{ mAdc}$, $f = 1.0\text{ GHz}$) ($V_{CE} = 8.0\text{ Vdc}$, $I_C = 50\text{ mAdc}$, $f = 1.0\text{ GHz}$)	MPS571 MMBR571LT1 MRF5711LT1, MRF571	f_T	— — —	6.0 8.0 8.0	— — —	GHz

FUNCTIONAL TESTS

Gain @ Noise Figure ($I_C = 10\text{ mAdc}$, $V_{CE} = 6.0\text{ Vdc}$)	MRF571 MRF571	$f = 0.5\text{ GHz}$ $f = 1.0\text{ GHz}$	G_{NF}	— 10	16.5 12	— —	dB
Noise Figure ($I_C = 10\text{ mAdc}$, $V_{CE} = 6.0\text{ Vdc}$)	MRF571 MRF571	$f = 0.5\text{ GHz}$ $f = 1.0\text{ GHz}$ $f = 2.0\text{ GHz}$	NF	— — —	1.0 1.5 2.8	— 2.0 —	dB
Gain @ Noise Figure ($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	MPS571 MMBR571LT1, T3 MRF5711LT1	$f = 0.5\text{ GHz}$ $f = 1.0\text{ GHz}$ $f = 0.5\text{ GHz}$ $f = 1.0\text{ GHz}$ $f = 1.0\text{ GHz}$	G_{NF}	— — — — —	14 9.0 16.5 10.5 13.5	— — — — —	dB
Noise Figure ($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	MPS571 MMBR571LT1, T3 MRF5711LT1	$f = 0.5\text{ GHz}$ $f = 1.0\text{ GHz}$ $f = 0.5\text{ GHz}$ $f = 1.0\text{ GHz}$ $f = 1.0\text{ GHz}$	NF	— — — — —	2.0 2.6 2.0 2.6 2.2	— — — — —	dB
Noise Figure ($V_{CE} = 6.0\text{ V}$, $I_C = 10\text{ mA}$, $f = 1.0\text{ GHz}$)	MRF5711LT1	$f = 1.0\text{ GHz}$	NF_{min}	—	1.6	—	dB
Power Gain in 50 Ω System ($V_{CE} = 6.0\text{ V}$, $I_C = 10\text{ mA}$, $f = 1.0\text{ GHz}$)			IS_{21}^2	9.0	10	—	dB

TYPICAL CHARACTERISTICS
MPS571, MMBR571LT1, T3

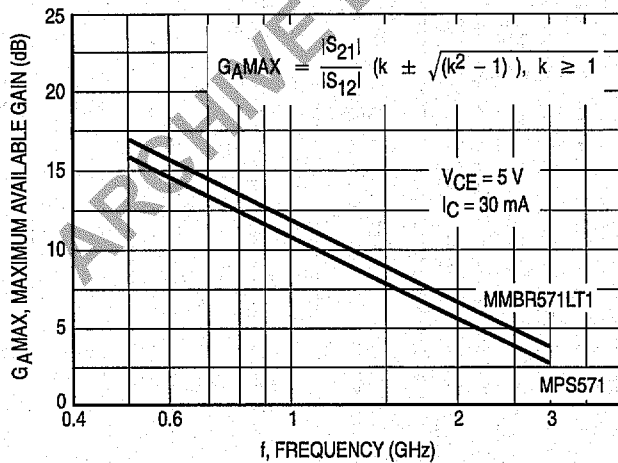


Figure 1. Maximum Available Gain versus Frequency

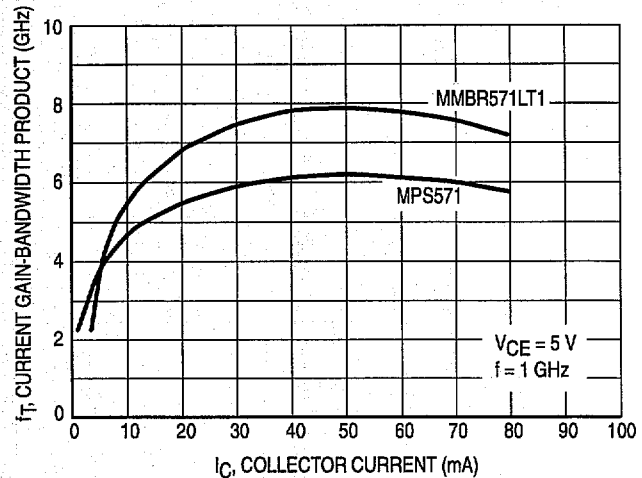


Figure 2. Current Gain-Bandwidth versus Collector Current @ 1.0 GHz

TYPICAL CHARACTERISTICS
MPS571, MMR571LT1, T3

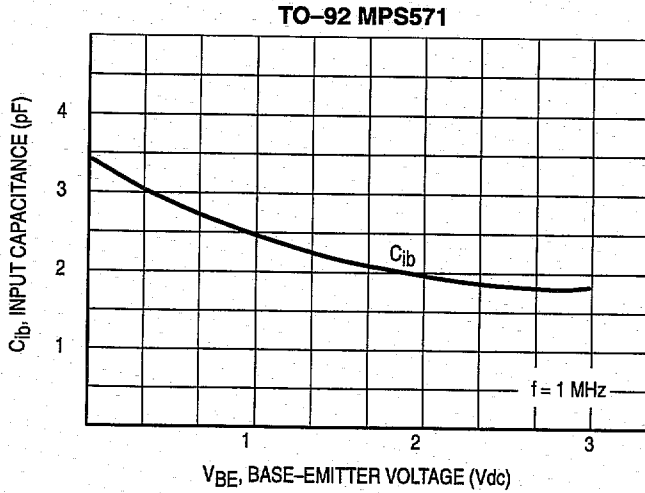


Figure 3. Input Capacitance versus Emitter Base Voltage

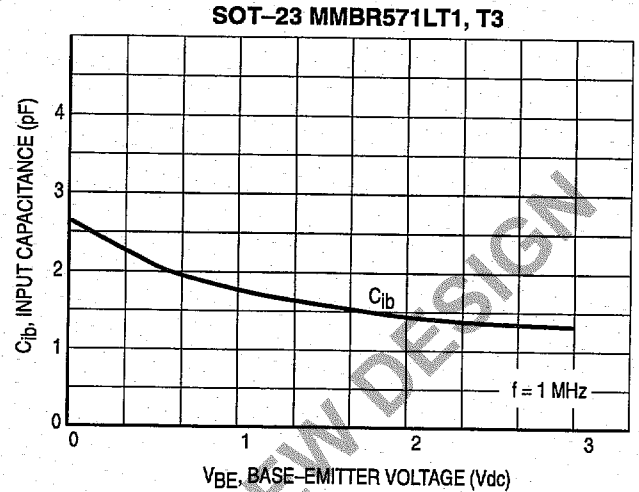


Figure 4. Input Capacitance versus Emitter Base Voltage

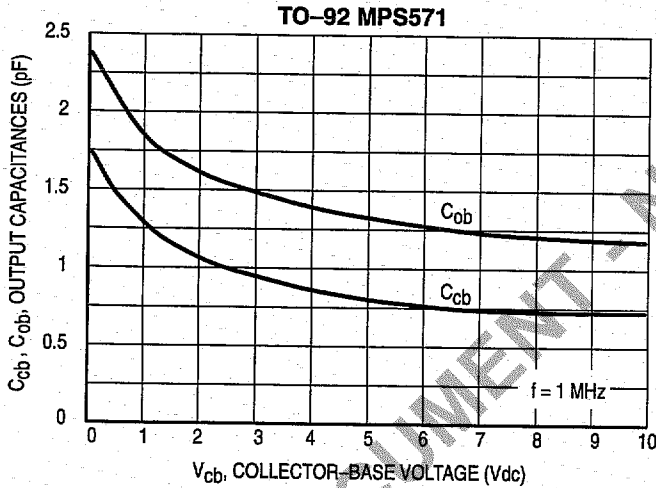


Figure 5. Output Capacitances versus Collector-Base Voltage

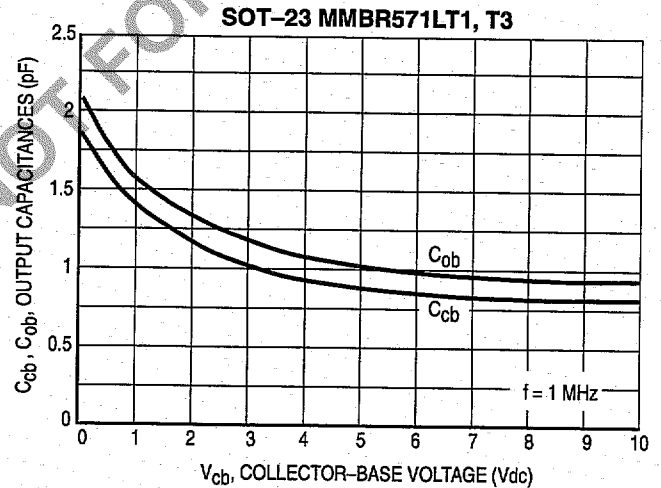


Figure 6. Output Capacitances versus Collector-Base Voltage

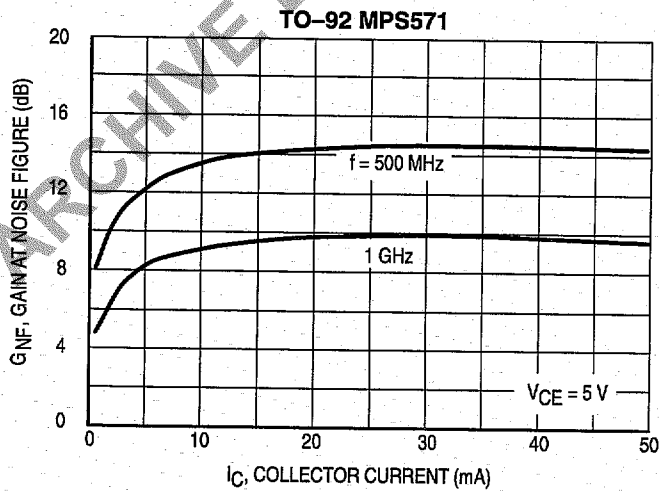


Figure 7. Gain at Noise Figure versus Collector Current

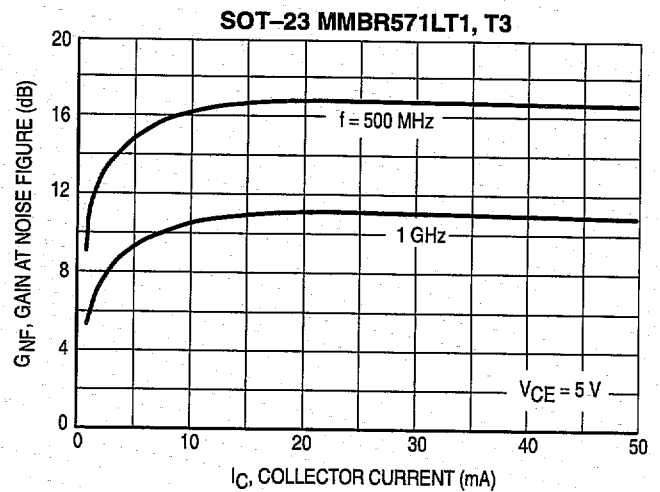


Figure 8. Gain at Noise Figure versus Collector Current

TYPICAL CHARACTERISTICS
MPS571, MMBR571LT1, T3

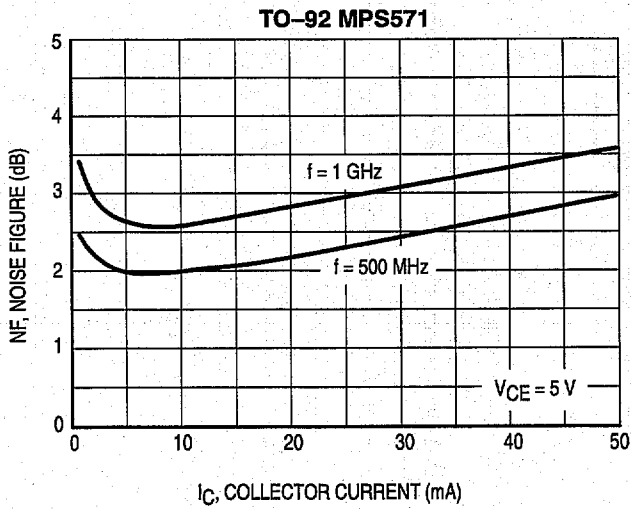


Figure 9. Noise Figure versus Collector Current

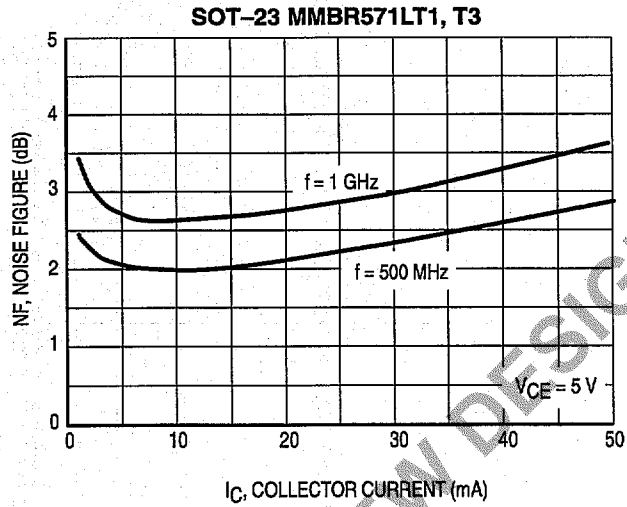


Figure 10. Noise Figure versus Collector Current

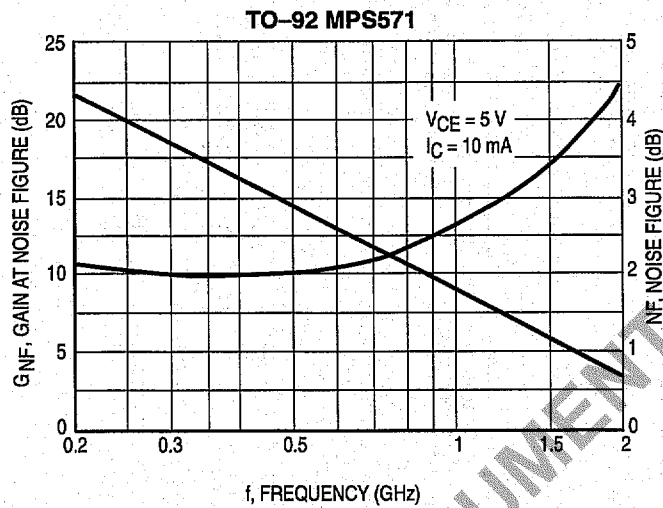


Figure 11. Gain at Noise Figure and Noise Figure versus Frequency

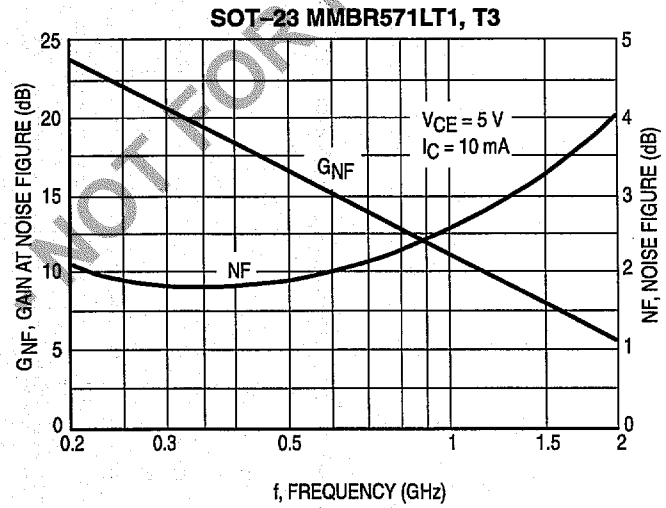


Figure 12. Gain at Noise Figure and Noise Figure versus Frequency

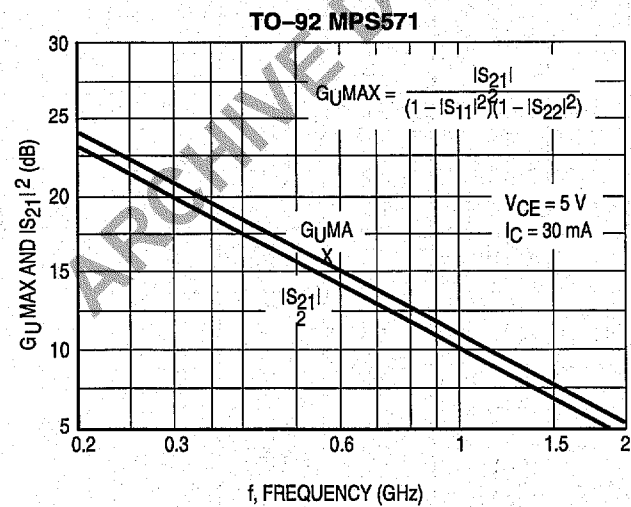


Figure 13. Maximum Unilateral Gain and Insertion Gain versus Frequency

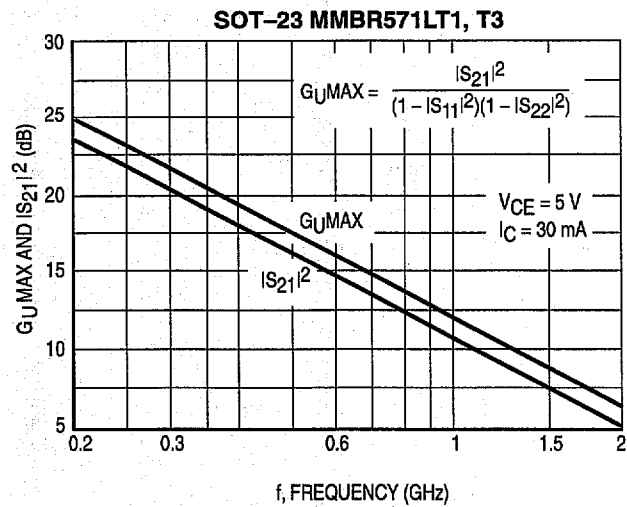


Figure 14. Maximum Unilateral Gain and Insertion Gain versus Frequency

TYPICAL CHARACTERISTICS
MRF5711LT1

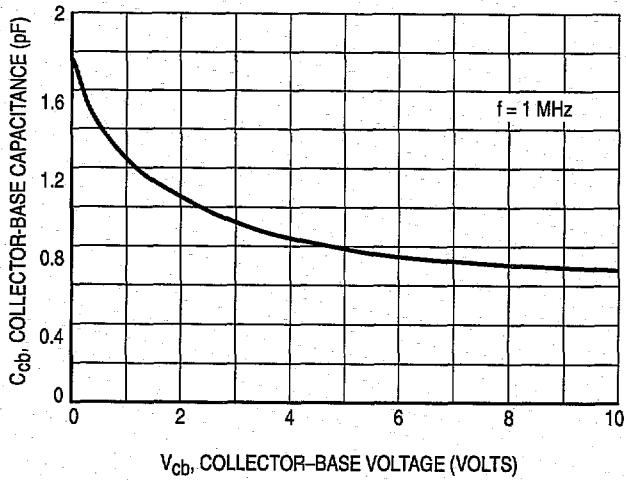


Figure 15. Collector-Base Capacitance versus Collector-Base Voltage

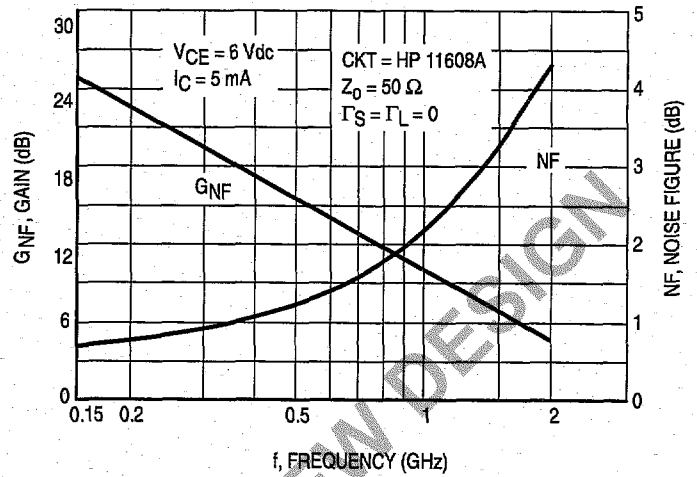


Figure 16. Gain and Noise Figure versus Frequency

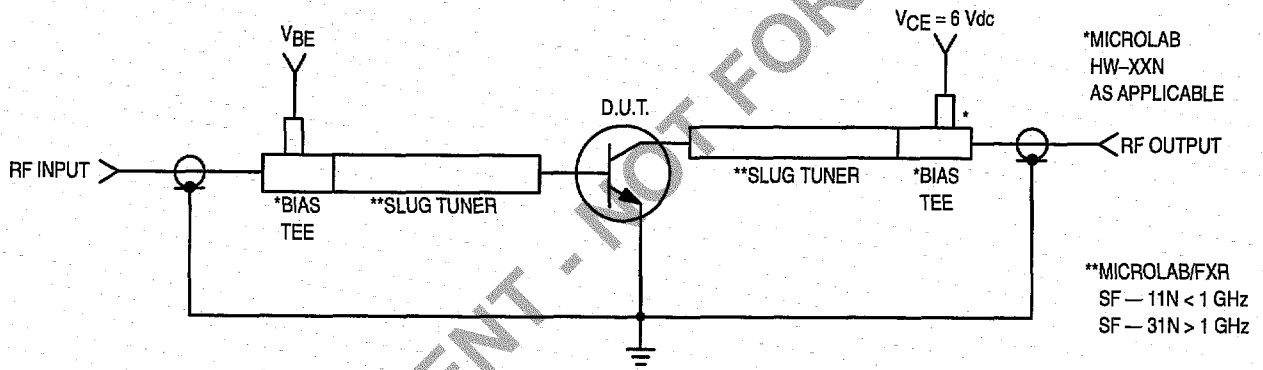


Figure 17. Functional Circuit Schematic

TYPICAL CHARACTERISTICS
MRF5711LT1

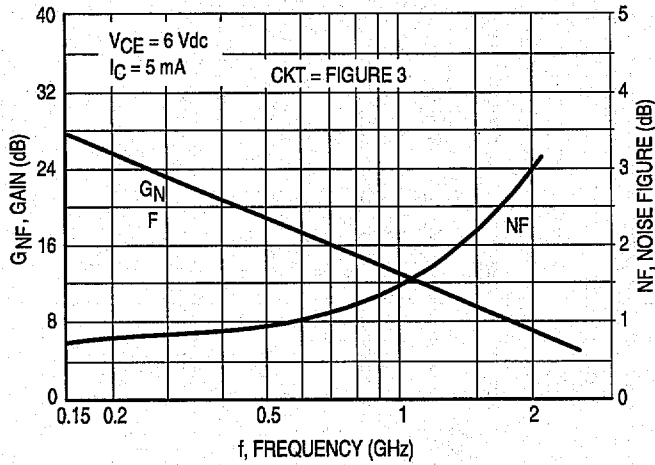


Figure 18. Gain and Noise Figure versus Frequency

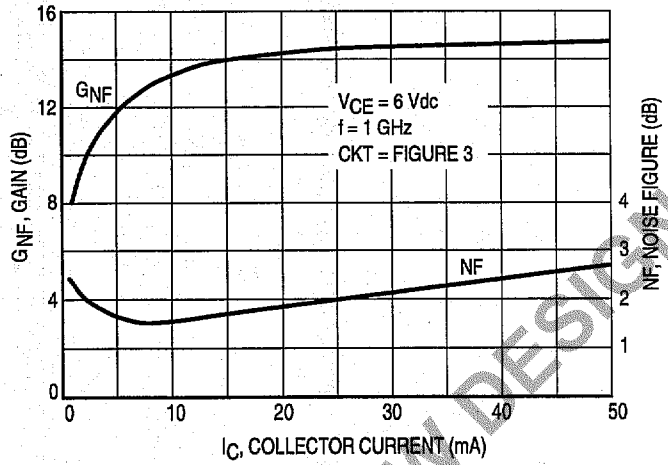


Figure 19. Gain and Noise Figure versus Collector Current

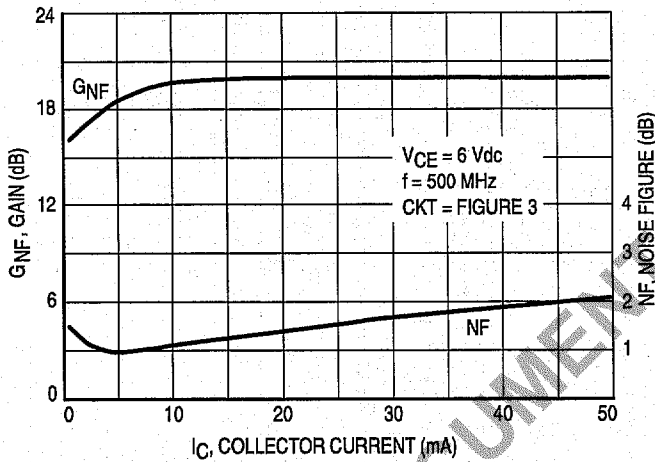


Figure 20. Gain and Noise Figure versus Collector Current

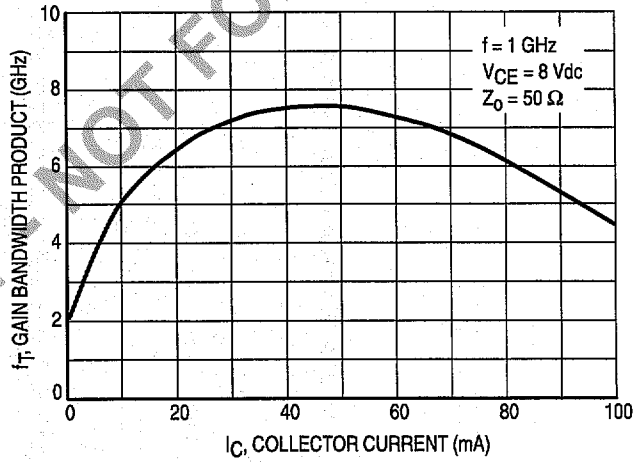


Figure 21. Gain Bandwidth Product versus Collector Current

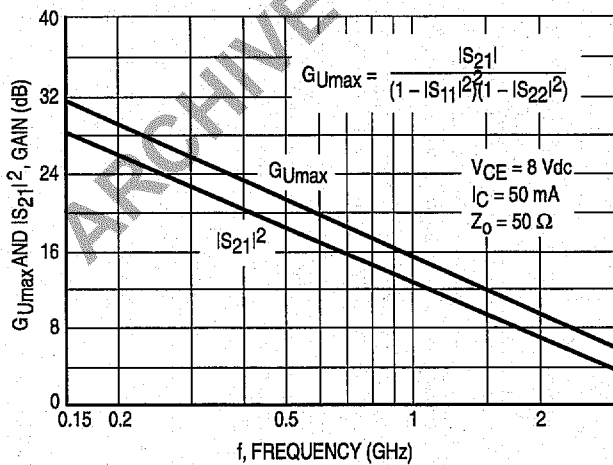


Figure 22. G_{Ummax} and $|S_{21}|^2$ versus Frequency

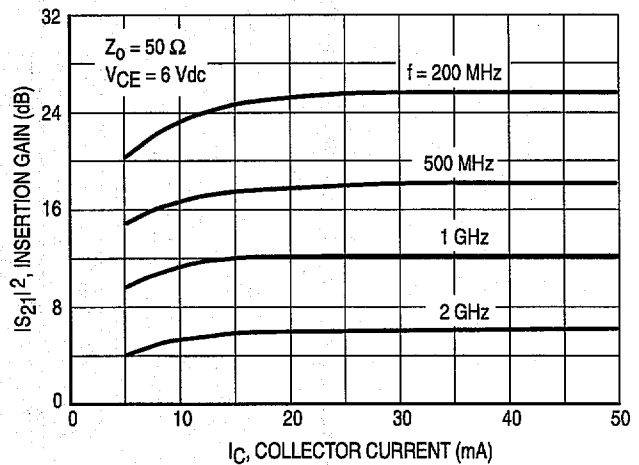


Figure 23. Insertion Gain versus Collector Current

MPS571

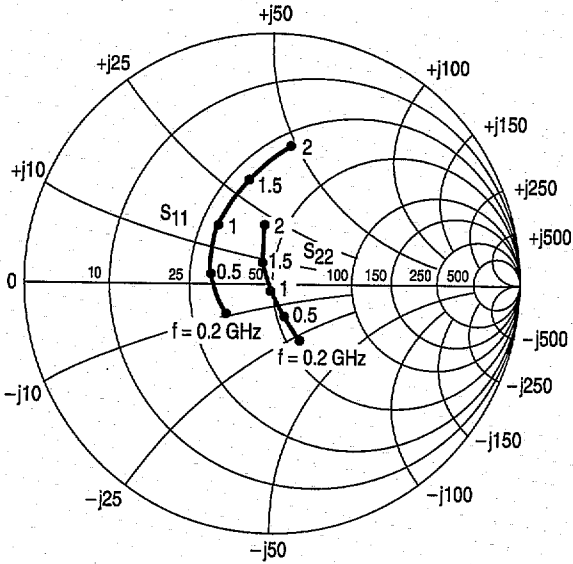


Figure 24. Input/Output Reflection Coefficients versus Frequency
 $V_{CE} = 5.0 \text{ V}$, $I_C = 30 \text{ mA}$

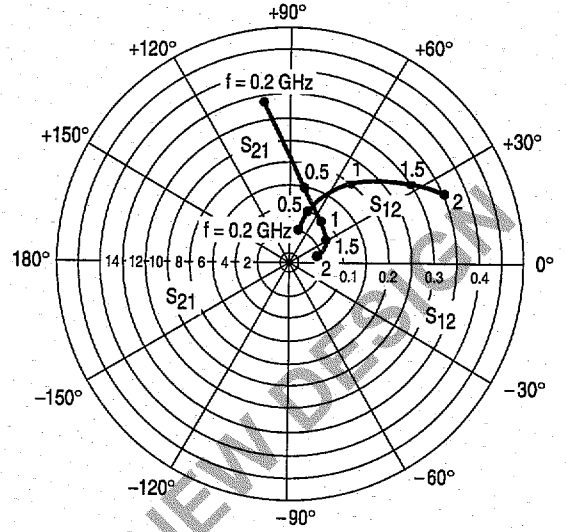


Figure 25. Forward/Reverse Transmission Coefficients versus Frequency
 $V_{CE} = 5.0 \text{ V}$, $I_C = 30 \text{ mA}$

VCE (Volts)	Ic (mA)	f (MHz)	S11		S21		S12		S22	
			S11	$\angle \phi$	S21	$\angle \phi$	S12	$\angle \phi$	S22	$\angle \phi$
5.0	5.0	200	0.62	-80	8.22	122	0.07	56	0.63	-44
		500	0.40	-148	4.52	87	0.11	50	0.36	-58
		1000	0.39	155	2.51	54	0.16	48	0.23	-78
		1500	0.46	122	1.86	32	0.23	42	0.15	-114
		2000	0.59	100	1.50	14	0.31	33	0.14	173
	15	200	0.33	-121	12.88	105	0.05	67	0.37	-59
		500	0.28	-175	5.62	79	0.10	65	0.18	-67
		1000	0.32	143	2.99	53	0.19	55	0.08	-94
		1500	0.40	117	2.14	32	0.27	42	0.07	171
		2000	0.55	95	1.74	17	0.35	30	0.198	117
	30	200	0.23	-143	13.65	99	0.05	75	0.26	-62
		500	0.23	169	5.75	76	0.11	70	0.13	-68
		1000	0.30	130	3.05	50	0.21	55	0.04	-136
		1500	0.41	106	2.11	28	0.29	38	0.12	130
		2000	0.56	85	1.70	11	0.36	23	0.26	102
	50	200	0.21	-158	13.96	96	0.05	79	0.21	-61
		500	0.23	162	5.82	75	0.11	72	0.11	-66
		1000	0.30	128	3.09	49	0.21	56	0.03	-149
		1500	0.41	105	2.11	28	0.29	39	0.12	127
		2000	0.56	84	1.70	11	0.36	23	0.27	100

Table 1. MPS571 Common Emitter S-Parameters

MMBR571LT1, T3

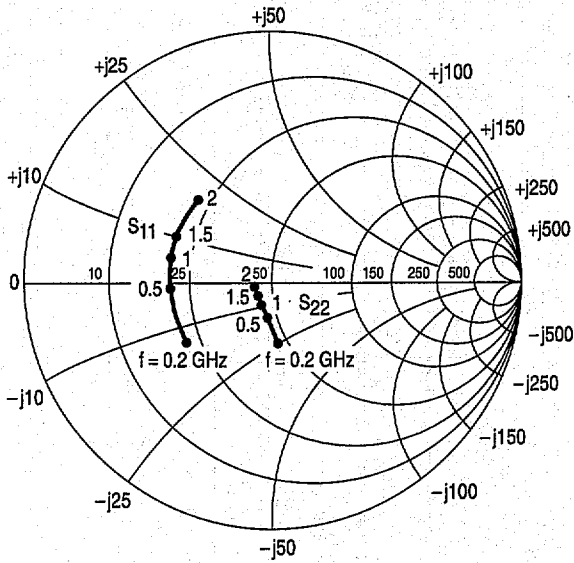


Figure 26. Input/Output Reflection Coefficients versus Frequency
 VCE = 5.0 V, IC = 30 mA

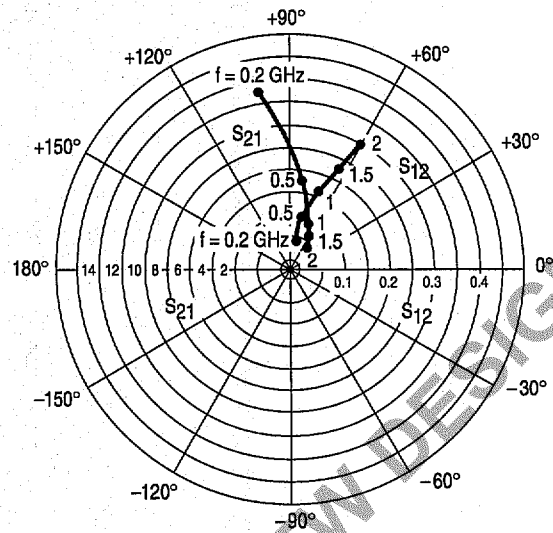
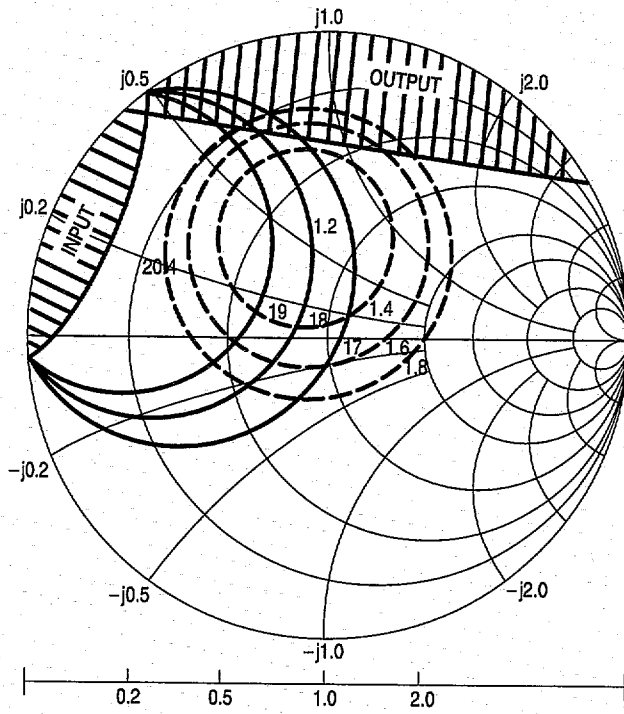


Figure 27. Forward/Reverse Transmission Coefficients versus Frequency
 VCE = 5.0 V, IC = 30 mA

VCE (Volts)	IC (mA)	f (MHz)	S11		S21		S12		S22	
			S11	∠φ	S21	∠φ	S12	∠φ	S22	∠φ
5.0	5.0	200	0.68	-82	8.41	126	0.07	53	0.61	-45
		500	0.52	-142	4.62	93	0.10	46	0.35	-60
		1000	0.50	179	2.57	72	0.14	53	0.26	-71
		1500	0.51	161	1.82	57	0.19	58	0.24	-77
		2000	0.52	143	1.48	45	0.24	59	0.22	-86
	15	200	0.46	-125	13.65	108	0.05	60	0.35	-73
		500	0.43	-169	6.03	86	0.09	66	0.17	-94
		1000	0.44	168	3.20	72	0.16	67	0.14	-111
		1500	0.45	152	2.21	58	0.22	64	0.11	-118
		2000	0.46	137	1.80	48	0.29	59	0.10	-131
	30	200	0.42	-148	14.79	102	0.04	68	0.26	-87
		500	0.41	-177	6.31	84	0.09	72	0.14	-115
		1000	0.42	165	3.35	71	0.16	70	0.12	-135
		1500	0.44	151	2.29	59	0.23	65	0.11	-144
		2000	0.44	135	1.84	48	0.30	60	0.10	-157
	50	200	0.41	-159	15.14	98	0.04	73	0.21	-96
		500	0.42	179	6.38	83	0.09	75	0.13	-124
		1000	0.43	163	3.35	70	0.16	71	0.12	-143
		1500	0.44	148	2.32	58	0.23	66	0.10	-151
		2000	0.45	134	1.84	48	0.30	60	0.09	-163

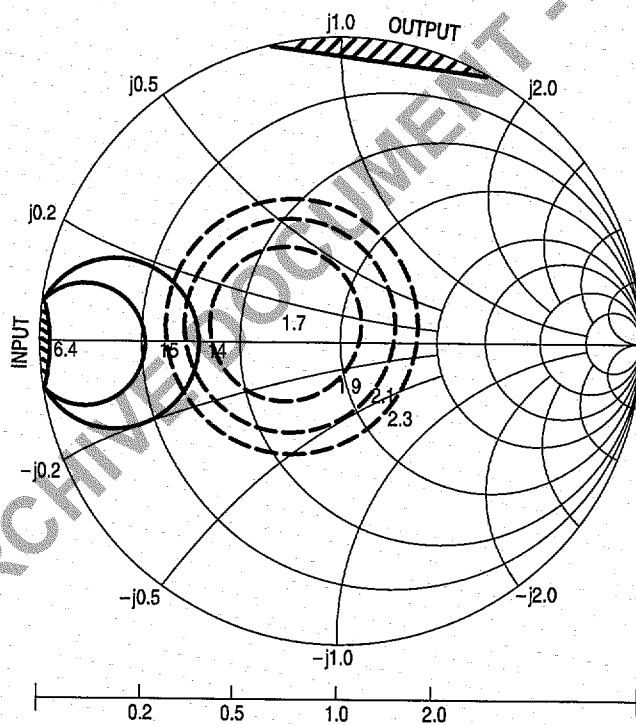
Table 2. MMBR571LT1 Common Emitter S-Parameters



$V_{CE} = 5\text{ V}$
 $I_C = 10\text{ mA}$
 [Shaded Area] = Area of Instability

f (GHz)	NF OPT	Γ_{MS} NF OPT	Rn	K
0.5	1.20 dB	$0.36 \angle 104^\circ$	7	0.63

Figure 28. MRF5711LT1 Constant Gain and Noise Figure Contours
(f = 0.5 GHz)



$V_{CE} = 5\text{ V}$
 $I_C = 10\text{ mA}$
 [Shaded Area] = Area of Instability

f (GHz)	NF OPT	Γ_{MS} NF OPT	Rn	K
1.0	1.70 dB	$0.20 \angle 162^\circ$	8	0.94

Figure 29. MRF5711LT1 Constant Gain and noise Figure Contours
(f = 1.0 GHz)

V _{CE} (Vdc)	I _C (mA)	f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
			S ₁₁	∠φ	S ₂₁	∠φ	S ₁₂	∠φ	S ₂₂	∠φ
6.0	5.0	200	0.79	-90	10.9	128	0.06	46	0.70	-45
		500	0.72	-144	5.7	96	0.08	28	0.42	-66
		1000	0.69	-177	3.0	75	0.09	28	0.31	-77
		1500	0.66	164	2.0	59	0.10	32	0.34	-89
		2000	0.65	147	1.6	47	0.12	38	0.32	-94
	10	200	0.72	-115	15.2	118	0.05	41	0.55	-66
		500	0.69	-160	6.9	92	0.06	34	0.30	-92
		1000	0.67	174	3.6	74	0.08	42	0.21	-108
		1500	0.64	159	2.4	60	0.10	46	0.23	-114
		2000	0.64	143	1.8	49	0.12	50	0.20	-116
	50	200	0.67	-159	20	102	0.02	48	0.33	-111
		500	0.67	179	8.2	85	0.04	58	0.33	-142
		1000	0.66	174	3.8	72	0.07	65	0.21	-158
		1500	0.63	151	2.7	61	0.10	64	0.22	-158
		2000	0.58	138	2.1	51	0.14	62	0.17	-165
8.0	5.0	200	0.80	-87	11.1	130	0.06	47	0.71	-42
		500	0.72	-141	5.9	97	0.08	30	0.44	-60
		1000	0.70	-177	3.1	75	0.09	28	0.33	-68
		1500	0.66	166	2.1	60	0.10	32	0.35	-80
		2000	0.61	149	1.6	47	0.12	39	0.35	-85
	10	200	0.72	-113	15.6	119	0.05	42	0.56	-61
		500	0.68	-159	7.2	92	0.06	34	0.31	-82
		1000	0.66	175	3.7	74	0.08	41	0.21	-92
		1500	0.64	160	2.5	61	0.09	47	0.23	-101
		2000	0.60	144	2.0	49	0.13	50	0.21	-103
	50	200	0.66	-156	20.9	103	0.02	48	0.31	-101
		500	0.65	-179	8.6	85	0.04	58	0.19	-128
		1000	0.64	164	4.3	72	0.07	65	0.16	-144
		1500	0.61	153	2.9	61	0.10	65	0.17	-142
		2000	0.58	137	2.3	51	0.13	64	0.14	-145

Table 3. MRF5711LT1, T3 Common Emitter S-Parameters

TYPICAL CHARACTERISTICS
MRF571

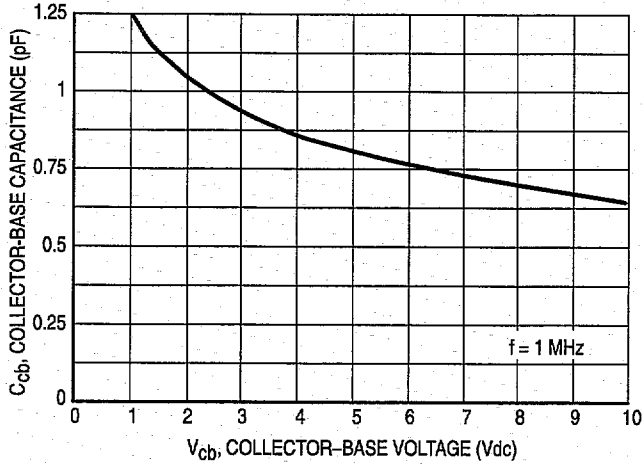


Figure 30. C_{cb} , Collector-Base Capacitance versus Voltage

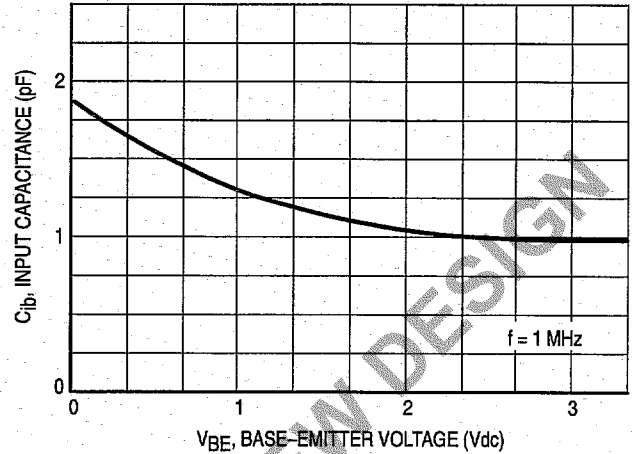


Figure 31. C_{ib} , Input Capacitance versus Emitter Base Voltage

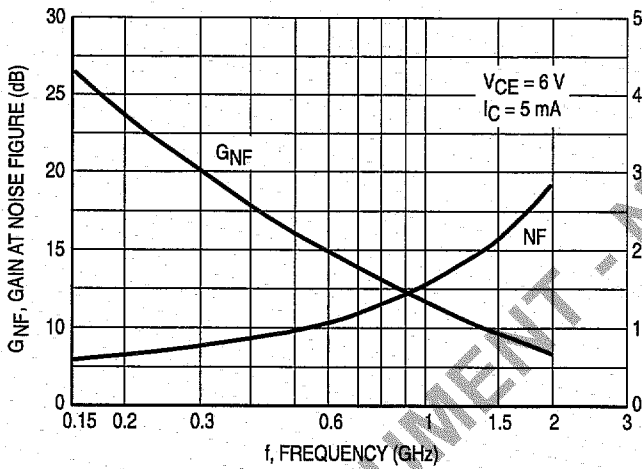


Figure 32. Gain at Noise Figure and Noise Figure versus Frequency

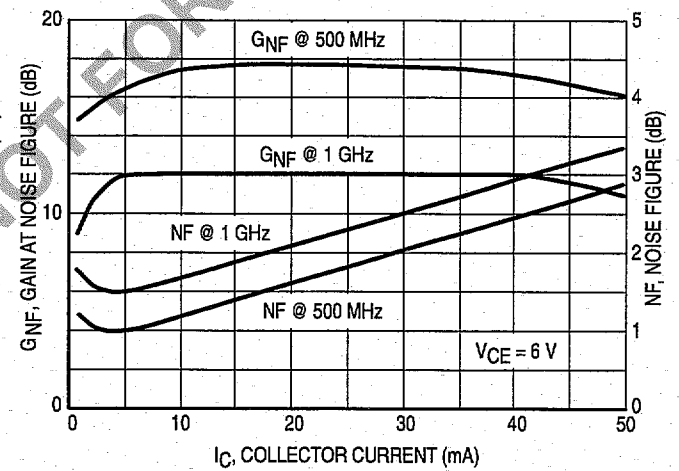


Figure 33. Gain at Noise Figure and Noise Figure versus Collector Current

TYPICAL CHARACTERISTICS
MRF571

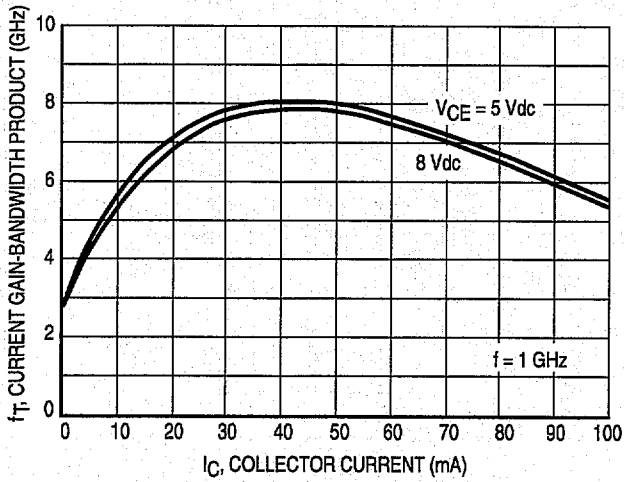


Figure 34. f_T , Current Gain-Bandwidth Product versus Collector Current

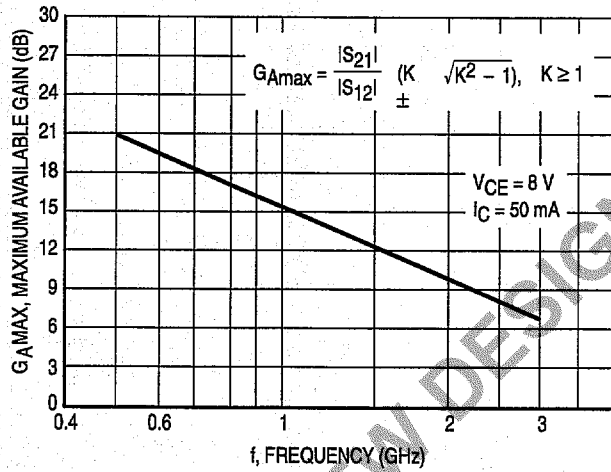


Figure 35. G_{Amax} , Maximum Available Gain versus Frequency

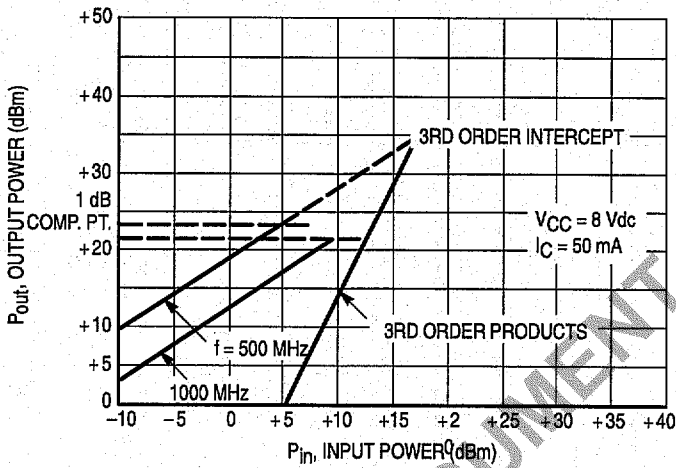


Figure 36. 1.0 dB Compression Point and Third Order Intercept

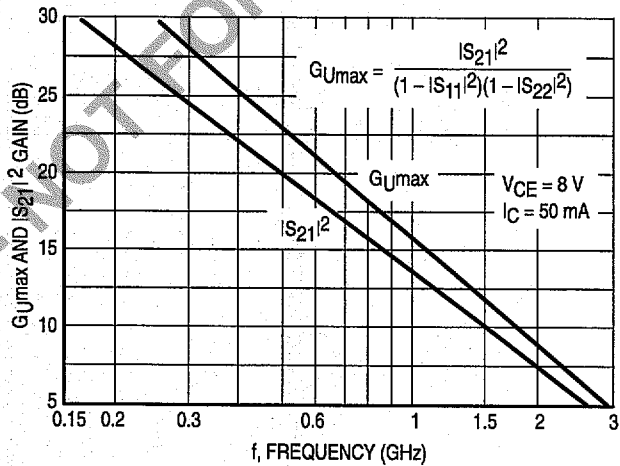


Figure 37. G_{Umax} and $|S_{21}|^2$ versus Frequency

MRF571

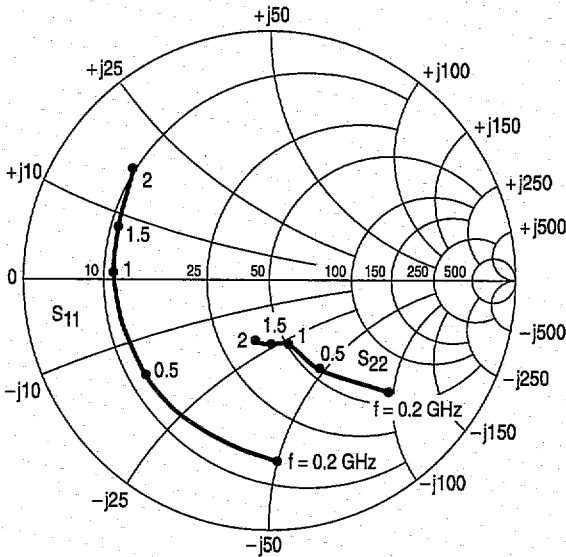


Figure 38. Input/Output Reflection Coefficients versus Frequency (GHz)
VCE = 6.0 V, IC = 5.0 mA

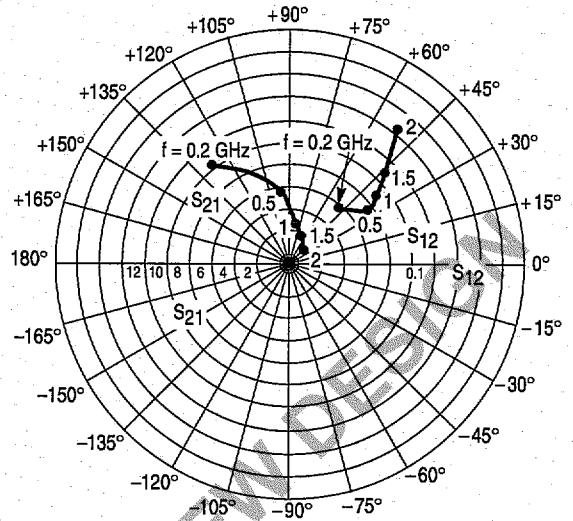
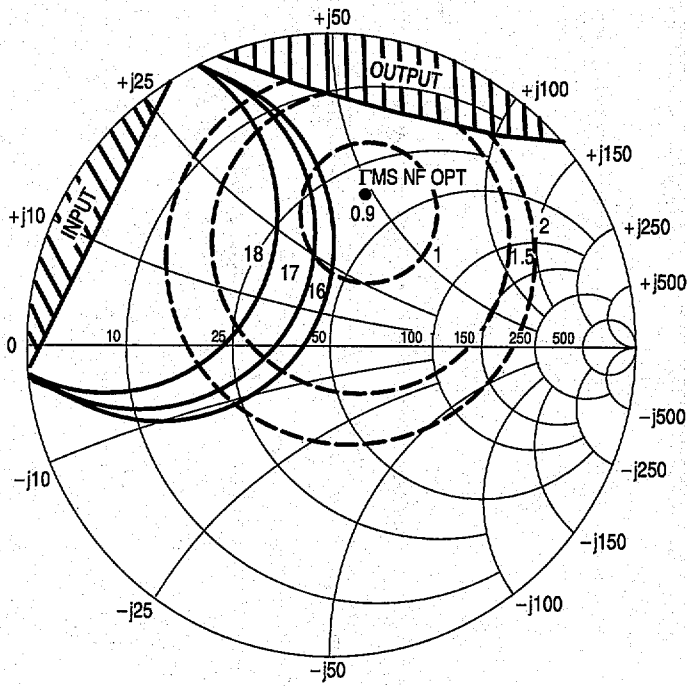


Figure 39. Forward/Reverse Transmission Coefficients versus Frequency (GHz)
VCE = 6.0 V, IC = 5.0 mA

VCE (Volts)	IC (mA)	f (MHz)	S11		S21		S12		S22	
			S11	∠φ	S21	∠φ	S12	∠φ	S22	∠φ
6.0	5	200	0.74	-86	10.5	129	0.06	48	0.69	-42
		500	0.62	-143	5.5	97	0.08	33	0.41	-59
		1000	0.61	178	3.0	78	0.09	37	0.28	-69
		1500	0.65	158	2.0	62	0.11	44	0.26	-88
		2000	0.70	140	1.6	51	0.14	51	0.27	-99
	10	200	0.64	-111	15	118	0.04	44	0.53	-59
		500	0.58	-160	6.9	93	0.06	42	0.27	-77
		1000	0.59	168	3.7	77	0.09	52	0.16	-91
		1500	0.63	151	2.5	64	0.12	56	0.16	-113
		2000	0.67	134	2.0	53	0.16	57	0.16	-118
	50	200	0.56	-160	20.4	102	0.02	57	0.27	-98
		500	0.57	176	8.4	86	0.05	67	0.14	-130
		1000	0.60	156	4.4	75	0.09	70	0.11	-164
		1500	0.62	152	2.9	64	0.13	68	0.13	-175
		2000	0.66	127	2.4	53	0.18	62	0.11	-178
8.0	5	200	0.75	-83	10.7	129	0.06	49	0.71	-39
		500	0.62	-140	5.1	98	0.08	34	0.43	-54
		1000	0.60	-179	3.7	78	0.09	38	0.31	-62
		1500	0.64	159	2.1	62	0.10	45	0.29	-80
		2000	0.69	141	1.7	52	0.13	52	0.29	-91
	10	200	0.64	-99	15.1	120	0.05	46	0.54	-60
		500	0.52	-152	7.1	94	0.07	45	0.32	-75
		1000	0.52	170	3.7	76	0.10	54	0.15	-82
		1500	0.52	150	2.5	62	0.13	56	0.16	-108
		2000	0.57	133	2.0	51	0.18	55	0.16	-107
	50	200	0.52	-153	19.6	102	0.03	56	0.28	-92
		500	0.52	178	8.1	86	0.05	67	0.16	-98
		1000	0.56	157	4.1	73	0.10	70	0.06	-130
		1500	0.54	139	2.8	62	0.13	68	0.11	-146
		2000	0.59	126	2.2	52	0.19	63	0.10	-137

Table 4. MRF571 Common Emitter S-Parameters

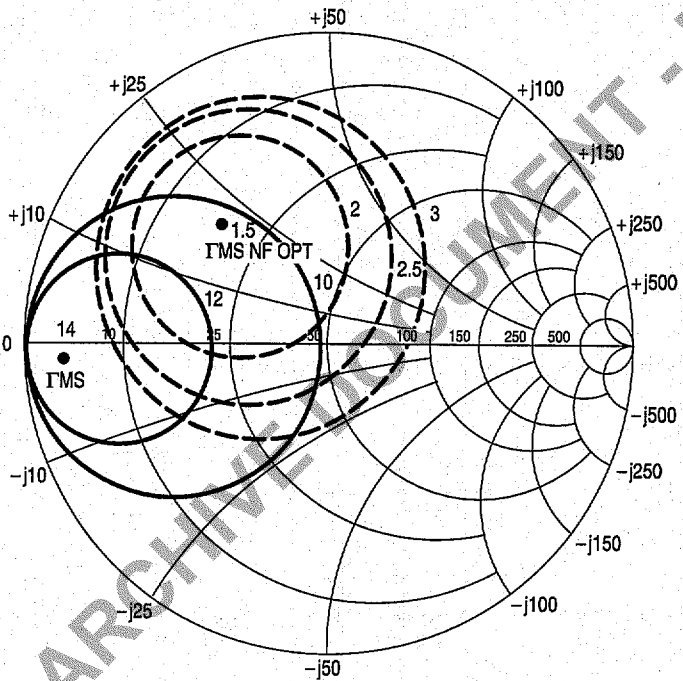


$V_{CE} = 6.0 \text{ V}$, $I_C = 5.0 \text{ mA}$
 $f = 500 \text{ MHz}$

▨ — REGION OF INSTABILITY

f (GHz)	NF OPT (dB)	Rn (Ω)	NF50 Ω (dB)
0.5	0.9	9.3	1.3

$\Gamma_{MS} \text{ NF OPT}$	K
$0.49 \angle 74^\circ$	0.58

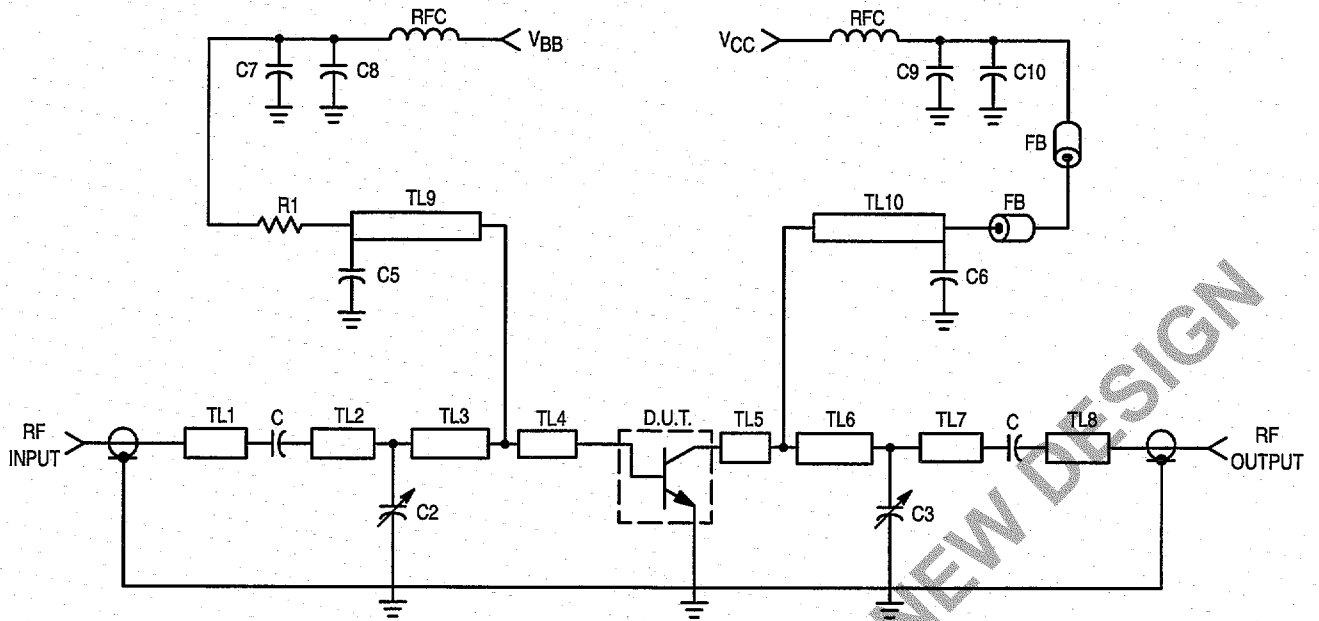


$V_{CE} = 6.0 \text{ V}$, $I_C = 5.0 \text{ mA}$
 $f = 1.0 \text{ GHz}$

f (GHz)	NF OPT (dB)	Rn (Ω)	NF50 Ω (dB)	$\Gamma_{MS} \text{ NF OPT}$
1.0	1.5	7.5	2.2	$0.48 \angle 134^\circ$

Γ_{MS}	Γ_{ML}
$0.89 \angle -179^\circ$	$0.81 \angle 66^\circ$

Figure 40. MRF571 Constant Gain and Noise Figure Contours

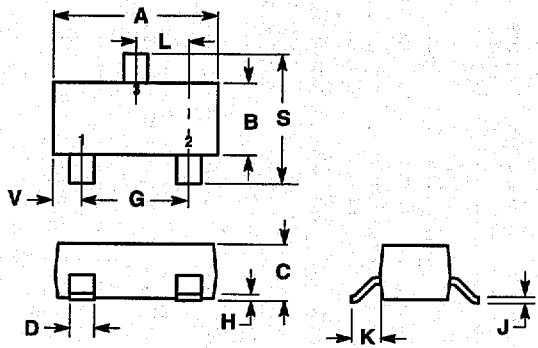


C1, C4, C5, C6, C8, C9 — 100 pF Chip Capacitor
 C2, C3 — 0.8–8.0 pF Johanson Capacitor
 C7, C10 — 10 μ F Tantalum Capacitor
 R1 — 1.0 kOhms Res.
 RFC — VK-200, Ferroxcube
 FB — Ferrite Bead, Ferroxcube 56-590-65/3B
 Board Material — 0.0625" Glass Teflon, $\epsilon_r = 2.55$

TL1, TL7, TL8 — Microstrip 0.162" x 0.600"
 TL2 — Microstrip 0.162" x 1.060"
 TL3 — Microstrip 0.162" x 0.700"
 TL4, TL5 — Microstrip 0.162" x 0.440"
 TL6 — Microstrip 0.162" x 1.140"
 TL8, TL9 — Microstrip 0.020" x 2.130"

Figure 41. MRF571 Test Circuit Schematic

PACKAGE DIMENSIONS

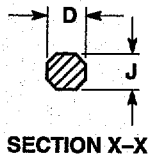
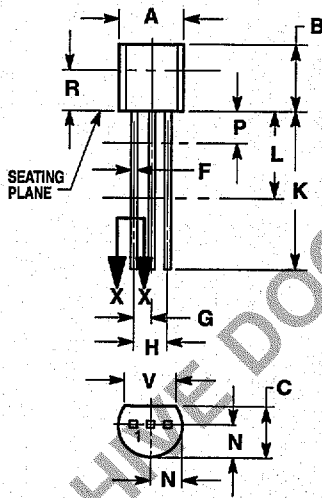


STYLE 6:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

CASE 318-07
ISSUE AD
MMBR571LT1

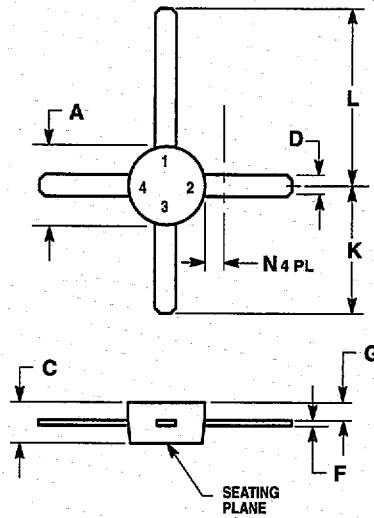


STYLE 2:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

CASE 29-04
ISSUE AD
MPS571

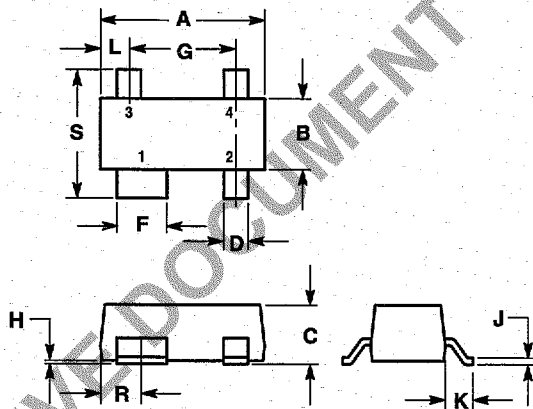


NOTES:
1. DIMENSION D NOT APPLICABLE IN ZONE N.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.44	5.21	0.175	0.205
C	1.90	2.54	0.075	0.100
D	0.84	0.99	0.033	0.039
F	0.20	0.30	0.080	0.012
G	0.76	1.14	0.030	0.045
K	7.24	8.13	0.285	0.320
L	10.54	11.43	0.415	0.450
N	—	1.65	—	0.065

STYLE 2:
PIN 1. COLLECTOR
2. EMITTER
3. BASE
4. EMITTER

CASE 317-01
ISSUE E
MRF571



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.80	3.04	0.110	0.120
B	1.20	1.39	0.047	0.055
C	0.64	1.14	0.033	0.045
D	0.39	0.50	0.015	0.020
F	0.79	0.93	0.031	0.037
G	1.78	2.03	0.070	0.080
H	0.013	0.10	0.0005	0.004
J	0.08	0.15	0.003	0.006
K	0.46	0.60	0.018	0.024
L	0.445	0.60	0.0175	0.024
R	0.72	0.83	0.028	0.033
S	2.11	2.48	0.083	0.098

STYLE 1:
PIN 1. COLLECTOR
2. EMITTER
3. EMITTER
4. BASE

CASE 318A-05
ISSUE J
MRF5711LT1


NOTES

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NOTES

ARCHIVE DOCUMENT - NOT FOR NEW DESIGN

PRELIMINARY DOCUMENT - NOT FOR NEW DESIGN

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